

substantially removing the titanium layer and any unreacted cobalt of the cobalt layer.

9. The method of Claim 8 further including, subsequent to the removing act, heating the body and cobalt silicide layer to reduce the resistivity of the cobalt silicide layer.

10. The method of Claim 9 wherein the heating act comprises rapidly thermally annealing the body and cobalt silicide layer.

11. The method of Claim 8 wherein the forming acts are performed in a chamber at below-atmospheric pressure without exposing the body to atmospheric pressure between the forming acts.

12. The method of Claim 8 wherein the titanium layer has a thickness of no more than 7.5  $\mu\text{m}$ .

13. The method of Claim 8 wherein the ionized physical vapor deposition comprises ion sputtering from a titanium target at a throw distance of at least 140 nm to the body.

14. The method of Claim 8 wherein the ionized physical vapor deposition is performed in a chamber with the body situated on a pedestal coupled to a bias source that provides AC current for helping ionize gas to produce gas ions that dislodge titanium from a titanium target in the chamber.

15. The method of Claim 8 wherein the ionized physical vapor deposition is performed in a chamber with the body situated on a pedestal coupled to a bias source that is turned substantially off to reduce resputtering of cobalt of the cobalt layer.

16. The method of Claim 8 wherein:

the body comprises (a) a region consisting largely of silicon and (b) a silicon oxide layer extending along the silicon region;

the method includes, prior to the forming acts, removing at least part of the silicon oxide layer to substantially expose at least part of the silicon region; and

at least part of the cobalt layer is formed along the silicon region where it is substantially exposed.

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17. The method of Claim 8 wherein:

the body comprises (a) a region consisting largely of silicon and (b) a silicon oxide layer situated along the silicon region; and

the reacting act includes causing oxygen in the silicon oxide layer to dissolve in the titanium layer.

18. The method of Claim 8 wherein:

the body comprises (i) a first region comprising silicon and (ii) a second region situated on the first region, an opening extending through the second region down to the first region;

the cobalt layer extends at least into the opening down to the first region; and

the titanium layer extends at least into the opening above material of the cobalt layer at the bottom of the opening.

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19. The method of Claim 18 wherein:

the first region comprises (a) a substrate region consisting largely of silicon and (b) a silicon oxide layer extending along the silicon substrate region at least at the bottom of the opening;

the method includes, prior to the forming acts, removing material of the silicon oxide layer at the bottom of the opening to substantially expose the silicon substrate region at the bottom of the opening; and

at least part of the cobalt layer is formed along the silicon substrate region at the bottom of the opening.

20. The method of Claim 18 wherein:

the first region comprises (a) a substrate region consisting largely of silicon and (b) a silicon oxide layer extending along the silicon substrate region at least at the bottom of the opening; and

the reacting act includes causing oxygen of the silicon oxide layer at the bottom of the opening to dissolve in the titanium layer.

21. The method of Claim 8 wherein the opening has an aspect ratio of at least 1.3.

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22. The method of Claim 18 wherein the opening has an aspect ratio of at least 2.5.

23. The method of Claim 8 wherein:

the body comprises an erasable programmable read-only memory region; and

the cobalt silicide layer is formed to contact a doped monocrystalline silicon section of erasable programmable read-only memory region.

24. The method of Claim 8 wherein:

the body comprises an erasable programmable read-only memory region that includes

(i) a first section comprising doped monocrystalline silicon and (ii) a second section situated on the first section, an opening extending through the second section down to the first section; and

the cobalt silicide layer is formed to contact the first section at the bottom of the opening.

25. The method of Claim 24 wherein the first section is a surface layer of the erasable programmable read-only memory region.--

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